

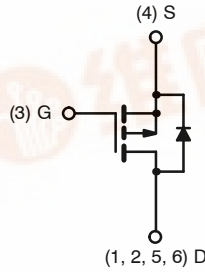
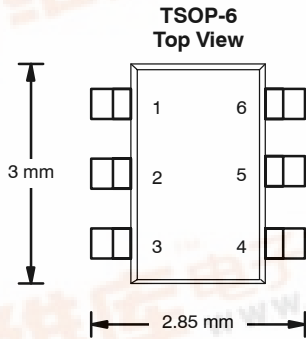


**Si3457BDV**  
Vishay Siliconix

**P-Channel 30-V (D-S) MOSFET**

**TrenchFET®**  
Power MOSFETs

PRODUCT SUMMARY		
V <sub>DS</sub> (V)	r <sub>DS(on)</sub> (Ω)	I <sub>D</sub> (A)
-30	0.054 @ V <sub>GS</sub> = -10 V	-5.0
	0.100 @ V <sub>GS</sub> = -4.5 V	-3.7



P-Channel MOSFET

Ordering Information: Si3457BDV-T1  
Si3457BDV-T1—E3 (Lead Free)

Marking Code: 7Bxxx

ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25°C UNLESS OTHERWISE NOTED)					
Parameter	Symbol	5 secs	Steady State	Unit	
Drain-Source Voltage	V <sub>DS</sub>	-30		V	
Gate-Source Voltage	V <sub>GS</sub>	±20			
Continuous Drain Current (T <sub>J</sub> = 150°C) <sup>a</sup>	I <sub>D</sub>	T <sub>A</sub> = 25°C	-5.0	-3.7	A
		T <sub>A</sub> = 70°C	-4.0	-3.0	
Pulsed Drain Current	I <sub>DM</sub>	-20		A	
Continuous Source Current (Diode Conduction) <sup>a</sup>	I <sub>S</sub>	-1.7	-0.95		
Maximum Power Dissipation <sup>a</sup>	P <sub>D</sub>	T <sub>A</sub> = 25°C	2.0	1.14	W
		T <sub>A</sub> = 70°C	1.3	0.73	
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to 150		°C	

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient <sup>a</sup>	R <sub>thJA</sub>	t ≤ 5 sec	53	62.5	°C/W
		Steady State	90	110	
Maximum Junction-to-Foot (Drain)	R <sub>thJF</sub>	25	36		

<sup>a</sup> Surface Mounted on 1" x 1" FR4 Board.

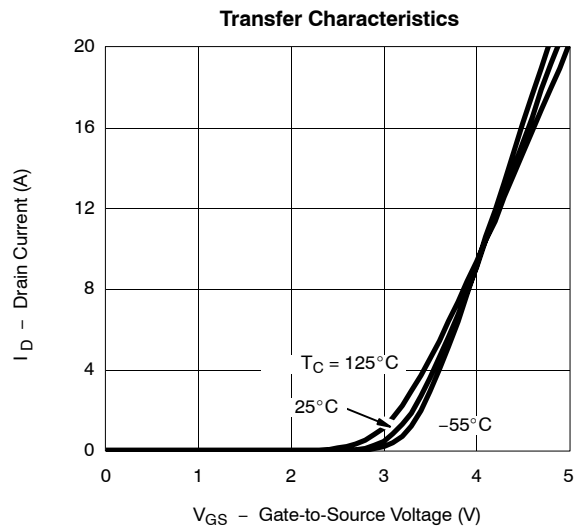
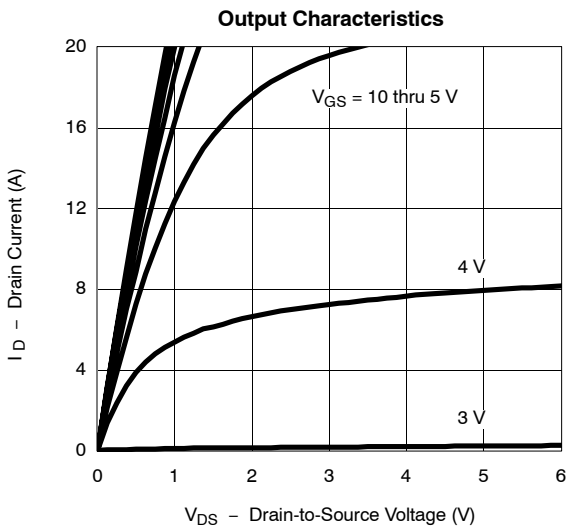


<b>SPECIFICATIONS (T<sub>J</sub> = 25 °C UNLESS OTHERWISE NOTED)</b>						
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
<b>Static</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250 μA	-1.0		-3	V
Gate-Body Leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ±20 V			±100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = -30 V, V <sub>GS</sub> = 0 V			-1	μA
		V <sub>DS</sub> = -30 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 85 °C			-5	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> ≤ -5 V, V <sub>GS</sub> = -10 V	-20			A
Drain-Source On-State Resistance <sup>a</sup>	r <sub>DS(on)</sub>	V <sub>GS</sub> = -10 V, I <sub>D</sub> = -5.0 A		0.044	0.054	Ω
		V <sub>GS</sub> = -4.5 V, I <sub>D</sub> = -3.7 A		0.082	0.100	
Forward Transconductance <sup>a</sup>	g <sub>fs</sub>	V <sub>DS</sub> = -15 V, I <sub>D</sub> = -5.0 A		10		S
Diode Forward Voltage <sup>a</sup>	V <sub>SD</sub>	I <sub>S</sub> = -1.7 A, V <sub>GS</sub> = 0 V		-0.8	-1.2	V
<b>Dynamic<sup>b</sup></b>						
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> = -15 V, V <sub>GS</sub> = -10 V, I <sub>D</sub> = -5.0 A		12.5	19	nC
Gate-Source Charge	Q <sub>gs</sub>			2.1		
Gate-Drain Charge	Q <sub>gd</sub>			3.5		
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> = -15 V, R <sub>L</sub> = 15 Ω I <sub>D</sub> ≅ -1 A, V <sub>GEN</sub> = -10 V, R <sub>g</sub> = 6 Ω		7	15	ns
Rise Time	t <sub>r</sub>			10	15	
Turn-Off Delay Time	t <sub>d(off)</sub>			30	45	
Fall Time	t <sub>f</sub>			22	35	
Source-Drain Reverse Recovery Time	t <sub>rr</sub>		I <sub>F</sub> = -1.7 A, di/dt = 100 A/μs		25	

**Notes**

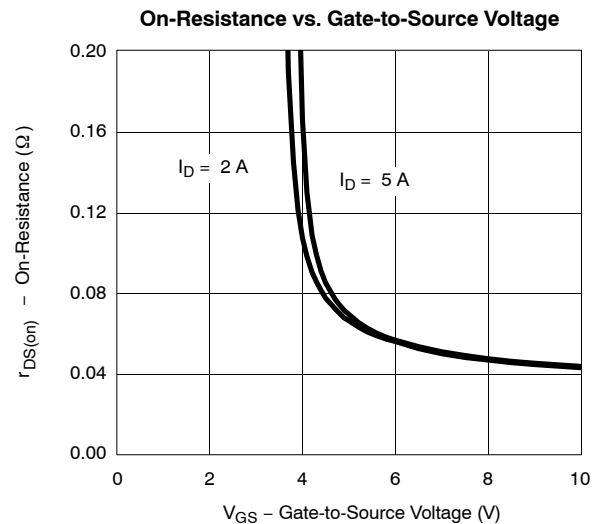
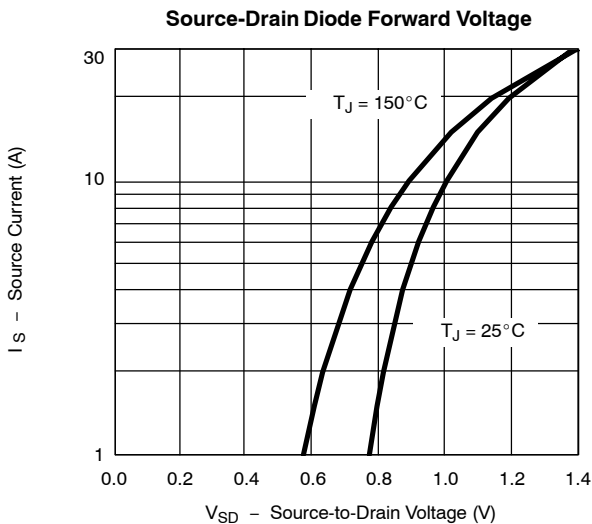
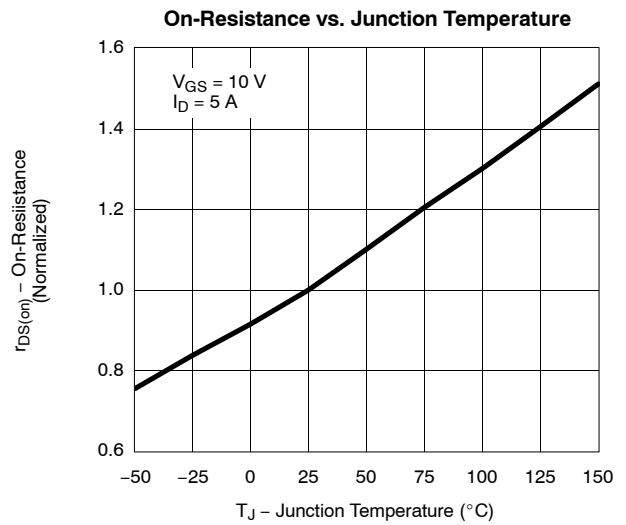
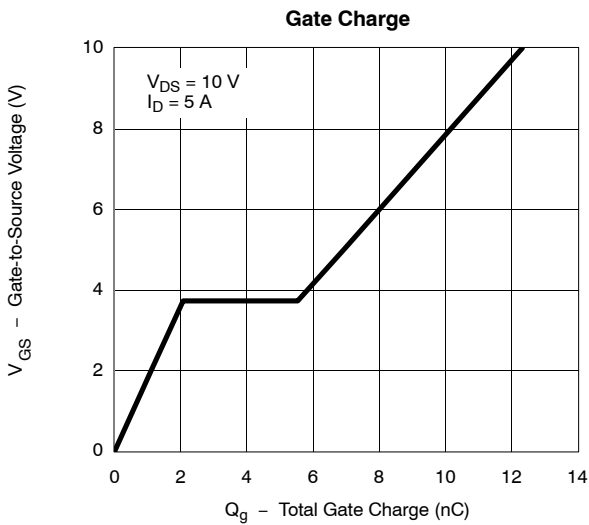
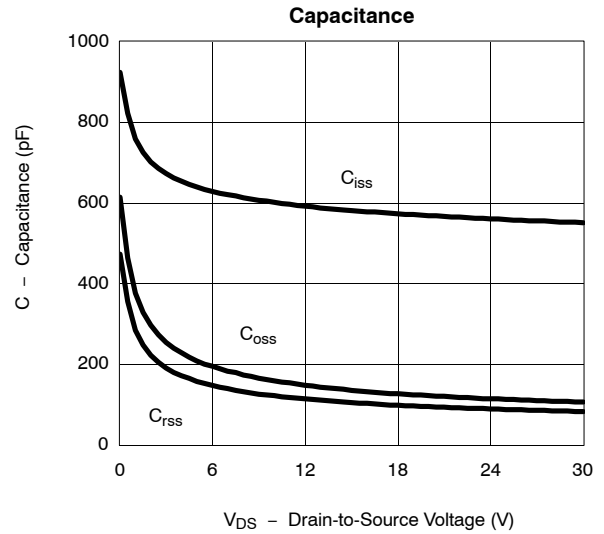
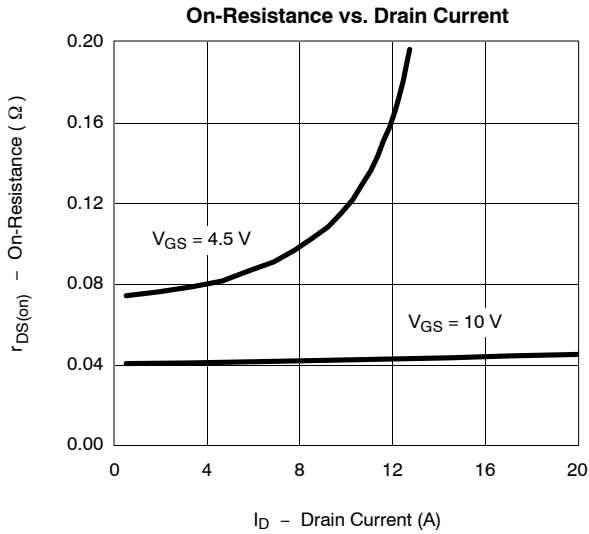
- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.
- b. Guaranteed by design, not subject to production testing.

**TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)**



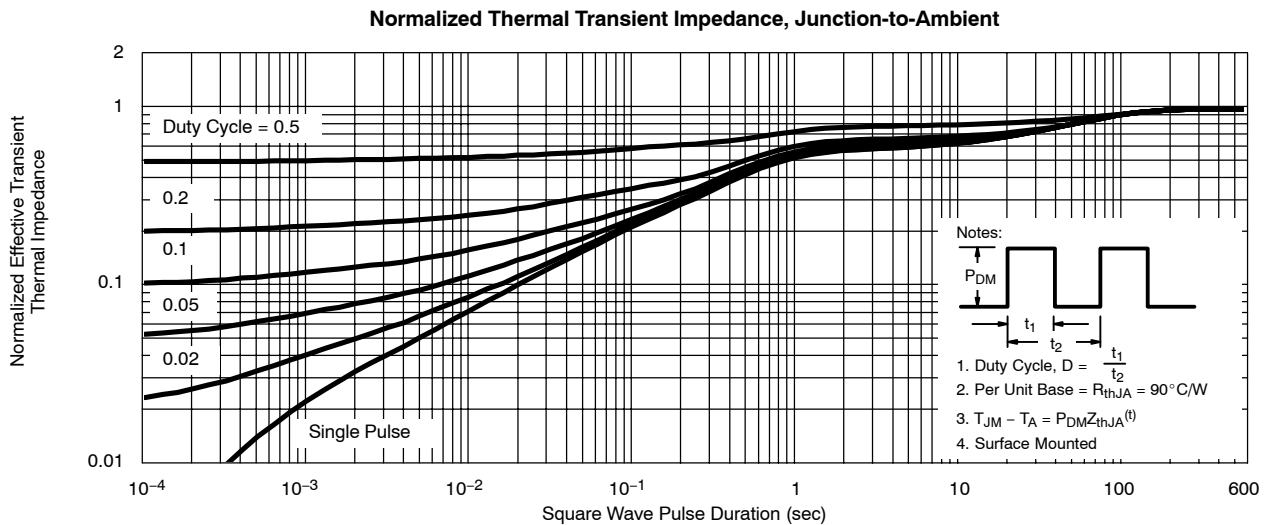
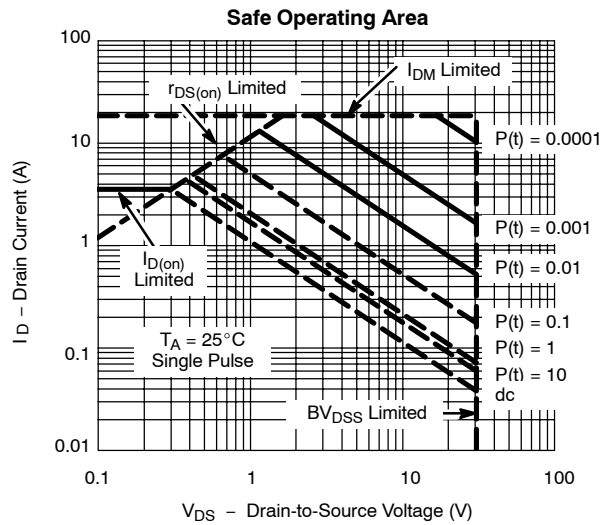
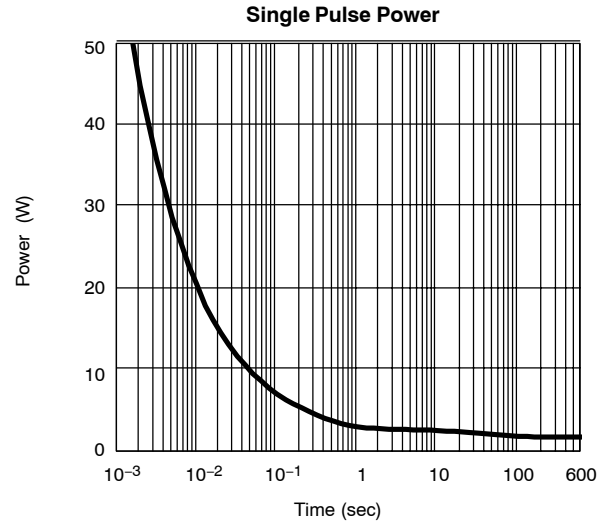
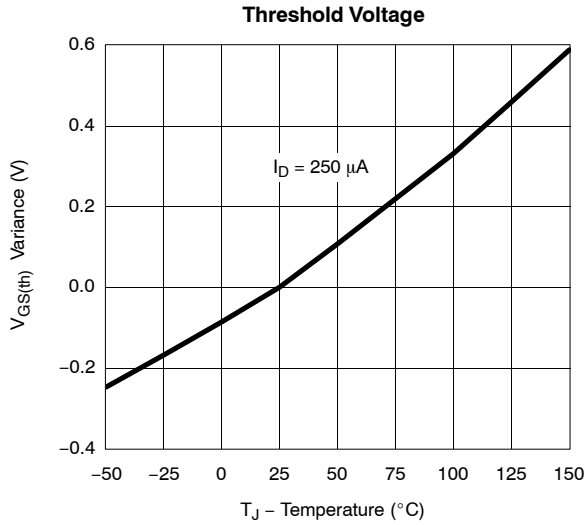


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